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BATTERY MONITORING IC FOR 3-SERIAL TO 5-SERIAL CELL PACK

Rev.1.3_00

The S-8255B Series is a monitoring IC for 3-serial to 5-serial cell lithium-ion rechargeable batteries, which includes high-accuracy voltage detection circuits and delay circuits. The S-8255B Series can monitor the status of 3-serial to 5-serial cell lithium-ion rechargeable battery packs.
Connecting an NTC, it allows for the temperature detection at four different points: high temperature detection during charging, low temperature detection during charging, high temperature detection during discharging, and low temperature detection during discharging.

■ Features

- High-accuracy voltage detection function for each cell

Overcharge detection voltage n (n = 1 to 5):	3.550 V to 4.600 V (50 mV step)	Accuracy ±20 mV
Overcharge release voltage n (n = 1 to 5):	3.150 V to 4.600 V*1	Accuracy ±50 mV
Overdischarge detection voltage n (n = 1 to 5):	2.000 V to 3.200 V (100 mV step)	Accuracy ±80 mV
Overdischarge release voltage n (n = 1 to 5):	2.000 V to 3.400 V*2	Accuracy ±100 mV

- Each delay time is settable by external capacitor (Temperature detection delay time is internally fixed)
- Independent control of charge inhibition, discharge inhibition, and power-saving by each control pin
- 0 V battery detection function is selectable: Available, unavailable
- CO and DO pin output voltage is limited to 8 V max. respectively
- Switching control for 3-serial to 5-serial cell is possible by inputting voltage to the SEL1 pin and the SEL2 pin
- Temperature detection is possible at four different points by connecting an NTC

High temperature detection ratio during charging / discharging:	0.600 to 0.900 (0.005 step)	Accuracy ±0.005
Low temperature detection ratio during charging / discharging:	0.030 to 0.400 (0.005 step)	Accuracy ±0.005

- High-withstand voltage: Absolute maximum rating 28 V
- Wide operation voltage range: 5 V to 24 V
- Wide operation temperature range: Ta = −40°C to +85°C
- Low current consumption
  - During operation: 19 μA max. (Ta = +25°C)
  - During power-saving: 0.1 μA max. (Ta = +25°C)
- Lead-free, halogen-free

***1.** Overcharge release voltage = Overcharge detection voltage − Overcharge hysteresis voltage
(Overcharge hysteresis voltage n (n = 1 to 5) is selectable in 0 V to 0.4 V in 50 mV step)
***2.** Overdischarge release voltage = Overdischarge detection voltage + Overdischarge hysteresis voltage
(Overdischarge hysteresis voltage n (n = 1 to 5) is selectable in 0 V to 0.7 V in 100 mV step)

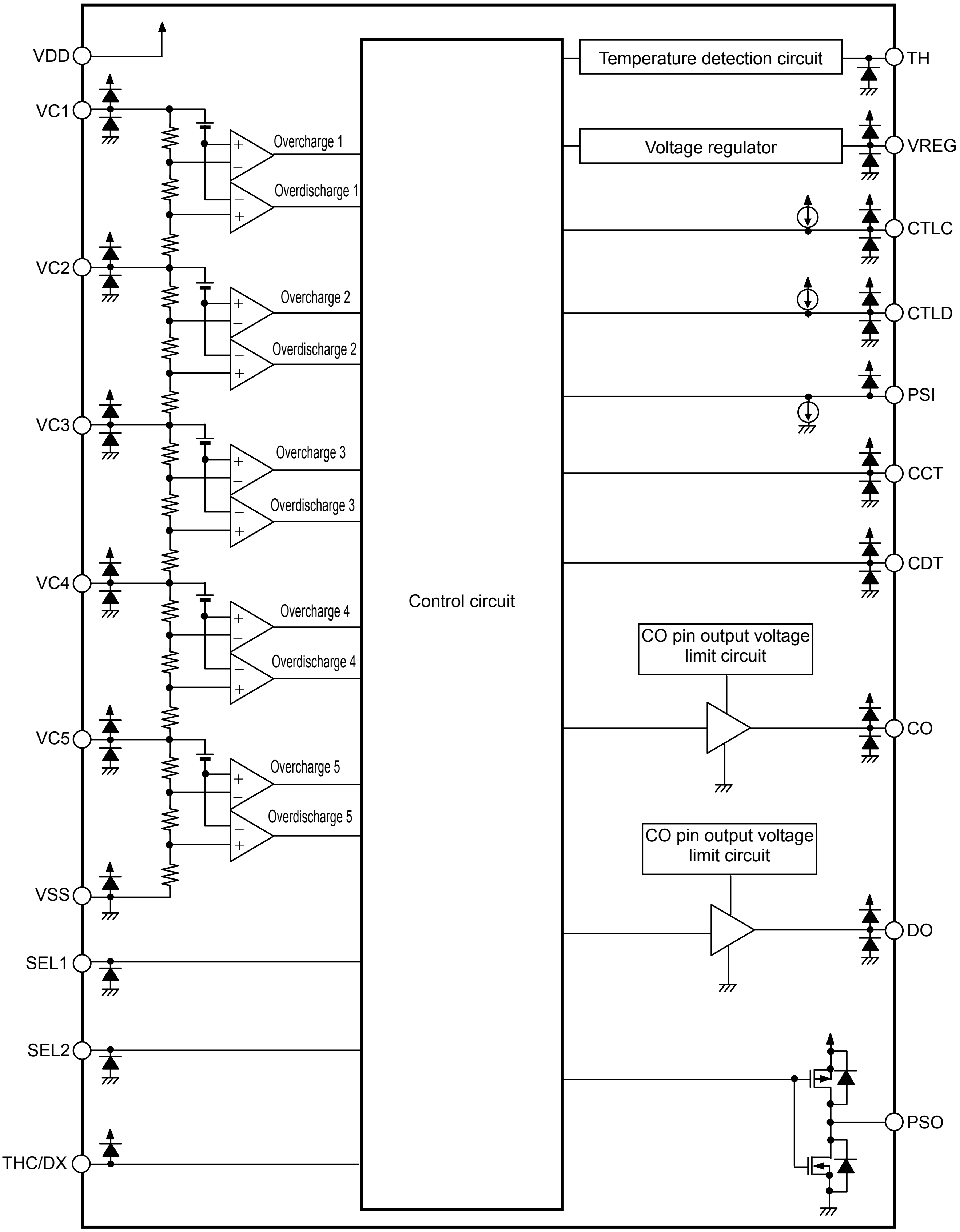
■ Application

- Rechargeable lithium-ion battery pack

■ Package

- 20-Pin TSSOP

■ Block Diagram



Remark Diodes in the figure are parasitic diodes.

Figure 1

■ Product Name Structure

1. Product name

S-8255B xx - TET1 S

- S: Environmental code
  - S: Lead-free, halogen-free
- TET1: Package abbreviation and IC packing specifications*1
  - TET1: 20-Pin TSSOP, Tape
- xx: Serial code*2
  - Sequentially set from AA to ZZ

***1.** Refer to the tape drawing.
***2.** Refer to "**3. Product name list**".

2. Package

Table 1 Package Drawing Code

Package Name	Dimension	Tape	Reel
20-Pin TSSOP	FT020-B-P-SD	FT020-B-C-SD	FT020-B-R-SD

3. Product name list

Table 2 (1 / 2)

Product Name	Overcharge Detection Voltage $[V_{CU}]$	Overcharge Release Voltage $[V_{CL}]$	Overdischarge Detection Voltage $[V_{DL}]$	Overdischarge Release Voltage $[V_{DU}]$	0 V Battery Detection Function*1
S-8255BAA-TET1S	4.100 V	4.050 V	2.600 V	2.700 V	Unavailable
S-8255BAB-TET1S	4.250 V	4.150 V	2.500 V	3.000 V	Available

Table 2 (2 / 2)

Product Name	High Temperature Detection Ratio during Charging $[r_{THCH}]$	Low Temperature Detection Ratio during Charging $[r_{THCL}]$	High Temperature Detection Ratio during Discharging $[r_{THDH}]$	Low Temperature Detection Ratio during Discharging $[r_{THDL}]$
S-8255BAA-TET1S	0.670	0.270	0.795	0.190
S-8255BAB-TET1S	0.670	0.270	0.795	0.190

***1.** 0 V battery detection function "available" / "unavailable" is selectable.

Remark Please contact our sales office for products other than those specified above.

■ Pin Configuration

1. 20-Pin TSSOP

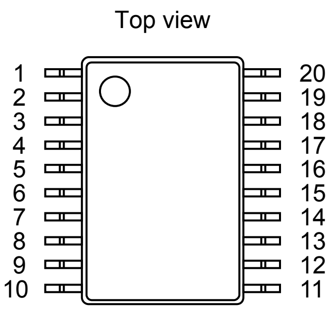


Figure 2

Table 3

Pin No.	Symbol	Description
1	TH	Input pin for temperature detection
2	VDD	Input pin for positive power supply, connection pin for positive voltage of battery 1
3	VC1	Connection pin for positive voltage of battery 1
4	VC2	Connection pin for negative voltage of battery 1, connection pin for positive voltage of battery 2
5	VC3	Connection pin for negative voltage of battery 2, connection pin for positive voltage of battery 3
6	VC4	Connection pin for negative voltage of battery 3, connection pin for positive voltage of battery 4
7	VC5	Connection pin for negative voltage of battery 4, connection pin for positive voltage of battery 5
8	VSS	Input pin for negative power supply, connection pin for negative voltage of battery 5
9	SEL1	Switching pins for number of cells in series [SEL1, SEL2] = ["L", "L"] : 5-serial cell [SEL1, SEL2] = ["L", "H"] : 4-serial cell [SEL1, SEL2] = ["H", "L"] : 3-serial cell [SEL1, SEL2] = ["H", "H"] : Setting inhibited
10	SEL2	
11	CCT	Capacitor connection pin for delay for overcharge detection voltage
12	CDT	Capacitor connection pin for delay for overdischarge detection voltage
13	PSO	Output pin for power-saving signal (CMOS output)
14	DO	Connection pin of discharge control FET gate (CMOS output)
15	CO	Connection pin of charge control FET gate (CMOS output)
16	THC/DX	Switching pin for detection temperature
17	CTLC	Control pin for CO pin output
18	CTLD	Control pin for DO pin output
19	PSI	Control pin for Power-saving
20	VREG	Voltage output pin for temperature detection

■ Absolute Maximum Ratings

Table 4

(Ta = +25°C unless otherwise specified)

Item	Symbol	Applied Pin	Absolute Maximum Rating	Unit
Input voltage between VDD pin and VSS pin	V_{DS}	VDD	V_{SS} − 0.3 to V_{SS} + 28	V
Input pin voltage	V_{IN}	VC1, VC2, VC3, VC4, VC5, CCT, CDT, SEL1, SEL2, TH, THC/DX, PSI, CTLC, CTLD	V_{SS} − 0.3 to V_{DD} + 0.3	V
Output pin voltage	V_{OUT}	CO, DO, PSO, VREG	V_{SS} − 0.3 to V_{DD} + 0.3	V
Operation ambient temperature	T_{opr}	−	−40 to +85	°C
Storage temperature	T_{stg}	−	−40 to +125	°C

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

■ Thermal Resistance Value

Table 5

Item	Symbol	Condition		Min.	Typ.	Max.	Unit
Junction-to-ambient thermal resistance[*1]	θ_{JA}	20-Pin TSSOP	Board A	−	68	−	°C/W
			Board B	−	59	−	°C/W
			Board C	−	−	−	°C/W
			Board D	−	−	−	°C/W
			Board E	−	−	−	°C/W

***1.** Test environment: compliance with JEDEC STANDARD JESD51-2A

Remark Refer to "**■ Power Dissipation**" and "**Test Board**" for details.

■ Electrical Characteristics

Table 6 (1 / 2)

(V1 = V2 = V3 = V4 = V5 = 3.5 V, Ta = +25°C unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	Test Circuit
Detection Voltage							
Overcharge detection voltage n (n = 1 to 5)	V_{CUn}	V1 = V2 = V3 = V4 = V5 = V_{CUn} − 0.050 V	V_{CUn} − 0.020	V_{CUn}	V_{CUn} + 0.020	V	1
Overcharge release voltage n (n = 1 to 5)	V_{CLn}	−	V_{CLn} − 0.050	V_{CLn}	V_{CLn} + 0.050	V	1
Overdischarge detection voltage n (n = 1 to 5)	V_{DLn}	−	V_{DLn} − 0.080	V_{DLn}	V_{DLn} + 0.080	V	1
Overdischarge release voltage n (n = 1 to 5)	V_{DUn}	−	V_{DUn} − 0.100	V_{DUn}	V_{DUn} + 0.100	V	1
Delay Time Function*1							
CCT pin internal resistance	R_{CCT}	V1 = V_{CU} + 0.025	6.15	8.31	10.20	MΩ	1
CDT pin internal resistance	R_{CDT}	V1 = V_{DL} − 0.085	615	831	1020	kΩ	1
CCT pin detection voltage	V_{CCT}	V1 = V_{CU} + 0.025	V_{DS} × 0.68	V_{DS} × 0.70	V_{DS} × 0.72	V	1
CDT pin detection voltage	V_{CDT}	V1 = V_{DL} − 0.085	V_{DS} × 0.68	V_{DS} × 0.70	V_{DS} × 0.72	V	1
Input Voltage							
Operation voltage between VDD pin and VSS pin	V_{DSOP}	Fixed output voltage of DO pin and CO pin	5	−	24	V	−
Input Current							
Current consumption during operation	I_{OPE}	−	−	10	19	μA	1
Current consumption during power-saving	I_{PSV}	−	−	−	0.1	μA	1
VC1 pin current	I_{VC1}	−	−	0.25	0.50	μA	1
VC2 pin current	I_{VC2}	−	−0.8	0.0	0.8	μA	1
VC3 pin current	I_{VC3}	−	−0.8	0.0	0.8	μA	1
VC4 pin current	I_{VC4}	−	−0.8	0.0	0.8	μA	1
VC5 pin current	I_{VC5}	−	−0.8	0.0	0.8	μA	1
Output Pin							
CO pin voltage "H"*2	V_{COH}	$V_{COH} < V_{DS}$	4.0	6.0	8.0	V	1
DO pin voltage "H"*3	V_{DOH}	$V_{DOH} < V_{DS}$	4.0	6.0	8.0	V	1
CO pin source current	I_{COH}	−	10	−	−	μA	1
CO pin sink current	I_{COL}	V1 = V2 = V3 = V4 = V5 = 5.6 V	10	−	−	μA	1
DO pin source current	I_{DOH}	−	10	−	−	μA	1
DO pin sink current	I_{DOL}	−	10	−	−	μA	1
PSO pin source current	I_{PSOH}	−	1	−	10	μA	1
PSO pin sink current	I_{PSOL}	V1 = V2 = V3 = V4 = V5 = 1.9 V	1	−	10	μA	1
0 V Battery Detection Function							
0 V battery detection voltage n (n = 1 to 5)	V_{0INHn}	0 V battery detection function "available"	1.0	1.3	1.5	V	1

***1.** Refer to "**4. Delay time setting**" in "**■ Operation**" for details of the delay time function.
***2.** When $V_{COH} \geq V_{DS}$, $V_{COH} = V_{DD}$
***3.** When $V_{DOH} \geq V_{DS}$, $V_{DOH} = V_{DD}$

Remark V_{DS}: Input voltage between VDD pin and VSS pin (V1 + V2 + V3 + V4 + V5)

Table 6 (2 / 2)

(V1 = V2 = V3 = V4 = V5 = 3.5 V, Ta = +25°C unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	Test Circuit
Control Pin							
SEL1 pin voltage "H"	V_{SEL1H}	–	V_{DS} × 0.95	–	–	V	–
SEL2 pin voltage "H"	V_{SEL2H}	–	V_{DS} × 0.95	–	–	V	–
SEL1 pin voltage "L"	V_{SEL1L}	–	–	–	V_{DS} × 0.05	V	–
SEL2 pin voltage "L"	V_{SEL2L}	–	–	–	V_{DS} × 0.05	V	–
CTLC pin reverse voltage	V_{CTLC}	–	0.1	0.7	2.0	V	1
CTLD pin reverse voltage	V_{CTLD}	–	0.1	0.7	2.0	V	1
PSI pin reverse voltage	V_{PSI}	–	0.1	4.0	8.0	V	1
CTLC pin response delay time	t_{CTLC}	–	0.275	0.500	0.725	ms	1
CTLD pin response delay time	t_{CTLD}	–	0.275	0.500	0.725	ms	1
PSI pin response delay time	t_{PSI}	–	0.3	0.9	3.0	ms	1
CTLC pin curent "H"	I_{CTLCH}	–	−0.1	0.0	0.1	μA	1
CTLC pin curent "L"	I_{CTLCL}	–	−0.45	−0.20	−0.05	μA	1
CTLD pin curent "H"	I_{CTLDH}	–	−0.1	0.0	0.1	μA	1
CTLD pin curent "L"	I_{CTLDL}	–	−0.45	−0.20	−0.05	μA	1
PSI pin curent "H"	I_{PSIH}	–	0.0	0.2	0.4	μA	1
PSI pin curent "L"	I_{PSIL}	–	−0.1	0.0	0.1	μA	1
Temperature Detection Function							
Output voltage for temperature detection	V_{REG}	Voltage between VDD pin and VREG pin	4.0	5.0	6.0	V	2
High temperature detection ratio during charging	r_{THCH}	$r_{THCH} = (V_{REG} - V_{TH}) / V_{REG}$	r_{THCH} − 0.005	r_{THCH}	r_{THCH} + 0.005	–	2
Low temperature detection ratio during charging	r_{THCL}	$r_{THCL} = (V_{REG} - V_{TH}) / V_{REG}$	r_{THCL} − 0.005	r_{THCL}	r_{THCL} + 0.005	–	2
High temperature detection ratio during discharging	r_{THDH}	$r_{THDH} = (V_{REG} - V_{TH}) / V_{REG}$	r_{THDH} − 0.005	r_{THDH}	r_{THDH} + 0.005	–	2
Low temperature detection ratio during discharging	r_{THDL}	$r_{THDL} = (V_{REG} - V_{TH}) / V_{REG}$	r_{THDL} − 0.005	r_{THDL}	r_{THDL} + 0.005	–	2
THC/DX pin voltage "H"	V_{THH}	–	V_{DS} − 2.0	V_{DS} −1.5	V_{DS} − 1.0	V	2
THC/DX pin voltage "L"	V_{THL}	–	0.5	1.0	1.5	V	2
Temperature detection delay time	t_{TH}	–	1.0	2.0	3.0	s	2

■ Test Circuits

Unless otherwise specified, for the CO pin output voltage (V_{CO}), DO pin output voltage (V_{DO}), and PSO pin output voltage (V_{PSO}), "L" or "H" is judged as follows.

L : $[V_{CO}, V_{DO}, V_{PSO}] \leq V_{DS} \times 0.1$ V
H : $[V_{CO}, V_{DO}, V_{PSO}] > V_{DS} \times 0.1$ V

Remark V_{DS}: Input voltage between VDD pin and VSS pin (V1 + V2 + V3 + V4 + V5)

1. Test circuit 1

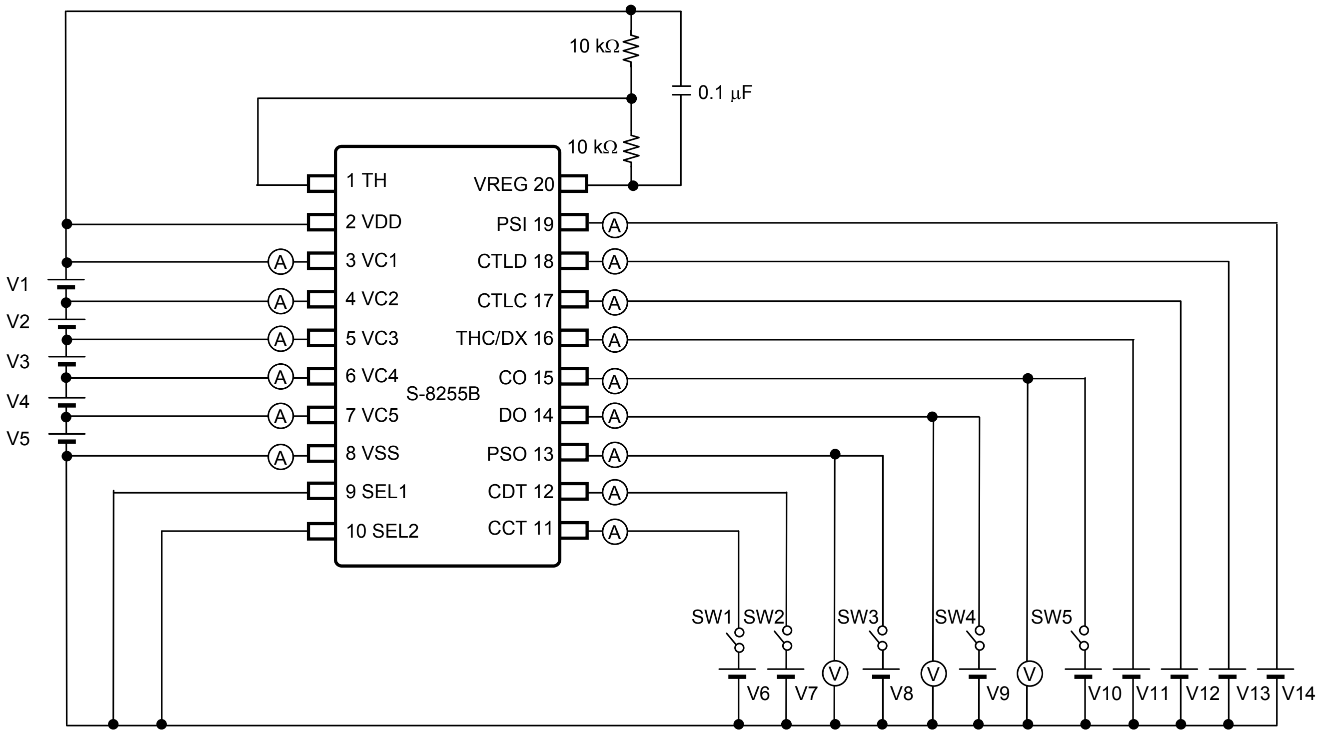


Figure 3 Test Circuit 1

This section provides explanations of Test items using Test circuit 1.
Perform each test after setting as shown in **Table 7**.

Table 7 Initial Setting of Test Circuit 1 (1 / 2)

V1	V2	V3	V4	V5	V6	V7	V8	V9	V10
3.5 V	3.5 V	3.5 V	3.5 V	3.5 V	–	–	–	–	–

Table 7 Initial Setting of Test Circuit 1 (2 / 2)

V11	V12	V13	V14	SW1	SW2	SW3	SW4	SW5
0 V	V_{DS}	V_{DS}	V_{DS}	OFF	OFF	OFF	OFF	OFF

1. 1 Overcharge detection voltage n (V_{CUn}), overcharge release voltage n (V_{CLn})

When the voltage V1 is gradually increased after setting V1 = V2 = V3 = V4 = V5 = V_{CUn} − 0.05 V and V_{CO} changes from "H" to "L", V1 is defined as the overcharge detection voltage 1 (V_{CU1}). When the voltage V1 is then gradually decreased and V_{CO} changes from "L" to "H", V1 is defined as the overcharge release voltage 1 (V_{CL1}).
Overcharge detection voltage n (V_{CUn}) and overcharge release voltage n (V_{CLn}) (n = 2 to 5) can be determined in the same way as when n = 1.

1. 2 Overdischarge detection voltage n (V_{DLn}), overdischarge release voltage n (V_{DUn})

When the voltage V1 is gradually decreased and V_{DO} changes from "H" to "L", V1 is defined as the overdischarge detection voltage 1 (V_{DL1}). When the voltage V1 is then gradually increased and V_{DO} changes from "L" to "H", V1 is defined as the overdischarge release voltage 1 (V_{DU1}).
Overdischarge detection voltage n (V_{DLn}) and overdischarge release voltage n (V_{DUn}) (n = 2 to 5) can be determined in the same way as when n = 1.

1. 3 CCT pin internal resistance (R_{CCT}), CCT pin detection voltage (V_{CCT})

The CCT pin internal resistance (R_{CCT}) is defined by R_{CCT} = V_{DS} / I_{CCT} under the set conditions of V1 = V_{CU1} + 0.025 V after setting V6 = 0 V and setting SW1 to ON. When the voltage V6 is then gradually increased and V_{CO} changes from "H" to "L", V6 is defined as the CCT pin detection voltage (V_{CCT}).

1. 4 CDT pin internal resistance (R_{CDT}), CDT pin detection voltage (V_{CDT})

The CDT pin internal resistance (R_{CDT}) is defined by R_{CDT} = V_{DS} / I_{CDT} under the set conditions of V1 = V_{DL1} − 0.085 V after setting V7 = 0 V and setting SW2 to ON. When the voltage V7 is then gradually increased and V_{DO} changes from "H" to "L", V7 is defined as the CDT pin detection voltage (V_{CDT}).

1. 5 Current consumption during operation (I_{OPE})

The current consumption during operation (I_{OPE}) is I_{VSS} under the initial setting shown in **Table 7**.

1. 6 Current consumption during power-saving (I_{PSV})

The current consumption during power-saving (I_{PSV}) is I_{VSS} when V14 = 0 V.

1. 7 CO pin source current (I_{COH})

The CO pin source current (I_{COH}) is I_{CO} when V10 = V_{COH} − 0.5 V and SW5 is ON.

1. 8 CO pin sink current (I_{COL})

The CO pin sink current (I_{COL}) is I_{CO} when V1 = V2 = V3 = V4 = V5 = 4.6 V, V10 = 0.5 V, and SW5 is ON.

1. 9 DO pin source current (I_{DOH})

The DO pin source current (I_{DOH}) is I_{DO} when V9 = V_{DOH} − 0.5 V and SW4 is ON.

1. 10 DO pin sink current (I_{DOL})

The DO pin sink current (I_{DOL}) is I_{DO} when V1 = V2 = V3 = V4 = V5 = 1.9 V, V9 = 0.5 V, and SW4 is ON.

1. 11 PSO pin source current (I_{PSOH})

The PSO pin source current (I_{PSOH}) is I_{PSO} when V14 = 0 V, V8 = V_{DS} − 0.5 V, and SW3 is ON.

1. 12 PSO pin sink current (I_{PSOL})

The PSO pin sink current (I_{PSOL}) is I_{PSO} when V8 = 0.5 V and SW3 is ON.

1. 13 0 V battery detection voltage n (V_{0INHn}) (0 V battery detection function "available")

When the voltage V1 is gradually decreased and V_{CO} changes from "H" to "L", V1 is defined as the 0 V battery detection voltage 1 (V_{0INH1}).
0 V battery detection voltage n (V_{0INHn}) (n = 2 to 5) can be determined in the same way as when n = 1.

1. 14 CTLC pin reverse voltage (V_{CTLC})

When the voltage V12 is gradually decreased and V_{CO} changes from "H" to "L", V12 is defined as the CTLC pin reverse voltage (V_{CTLC}).

1. 15 CTLD pin reverse voltage (V_{CTLD})

When the voltage V13 is gradually decreased and V_{DO} changes from "H" to "L", V13 is defined as the CTLD pin reverse voltage (V_{CTLD}).

1. 16 PSI pin reverse voltage (V_{PSI})

When the voltage V14 is gradually decreased and V_{PSO} changes from "L" to "H", V14 is defined as the PSI pin reverse voltage (V_{PSI}).

1. 17 CTLC pin response delay time (t_{CTLC})

The CTLC pin response delay time (t_{CTLC}) is the time period from when the voltage V12 changes to V12 = 0 V until when V_{CO} changes from "H" to "L".

1. 18 CTLD pin response delay time (t_{CTLD})

The CTLD pin response delay time (t_{CTLD}) is the time period from when the voltage V13 changes to V13 = 0 V until when V_{DO} changes from "H" to "L".

1. 19 PSI pin response delay time (t_{PSI})

The PSI pin response delay time (t_{PSI}) is the time period from when the voltage V14 changes to V14 = 0 V until when V_{PSO} changes from "L" to "H".

1. 20 CTLC pin current "H" (I_{CTLCH}), CTLC pin current "L" (I_{CTLCL})

The CTLC pin current "H" (I_{CTLCH}) is I_{CTLC} when V12 = V_{DS}.
The CTLC pin current "L" (I_{CTLCL}) is I_{CTLC} when V12 = 0 V.

1. 21 CTLD pin current "H" (I_{CTLDH}), CTLD pin current "L" (I_{CTLDL})

The CTLD pin current "H" (I_{CTLDH}) is I_{CTLD} when V13 = V_{DS}.
The CTLD pin current "L" (I_{CTLDL}) is I_{CTLD} when V13 = 0 V.

1. 22 PSI pin current "H" (I_{PSIH}), PSI pin current "L" (I_{PSIL})

The PSI pin current "H" (I_{PSIH}) is I_{PSI} when V14 = V_{DS}.
The PSI pin current "L" (I_{PSIL}) is I_{PSI} when V14 = 0 V.

2. Test circuit 2

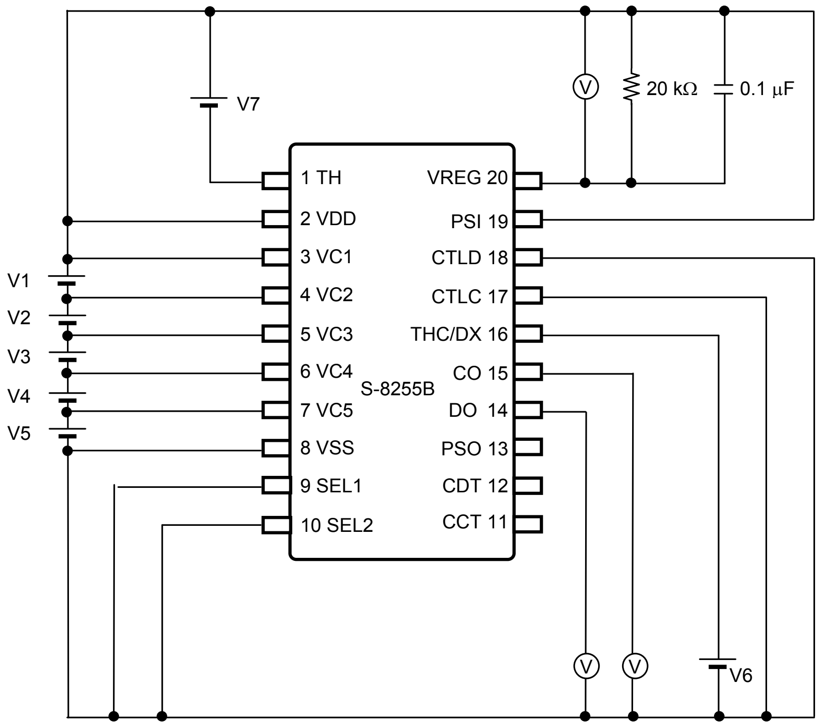


Figure 4 Test Circuit 2

This section provides explanations of Test items using Test circuit 2.
Perform each test after setting as shown in **Table 8**.

Table 8 Initial Setting of Test Circuit 2

V1	V2	V3	V4	V5	V6	V7*1
3.5 V	3.5 V	3.5 V	3.5 V	3.5 V	0 V	2.5 V

***1.** V7 is an absolute value.

2. 1 Output voltage for temperature detection (V_{REG})

The maximum voltage between the VDD pin and VREG pin is defined as the output voltage for temperature detection (V_{REG}).

2. 2 High temperature detection ratio during charging (r_{THCH})

When the voltage V7 is gradually decreased after setting V6 = V_{DS} and V_{CO} changes from "H" to "L", the high temperature detection ratio during charging (r_{THCH}) is defined by (V_{REG} − V7) / V_{REG}.

2. 3 Low temperature detection ratio during charging (r_{THCL})

When the voltage V7 is gradually increased after setting V6 = V_{DS} and V_{CO} changes from "H" to "L", the low temperature detection ratio during charging (r_{THCL}) is defined by (V_{REG} − V7) / V_{REG}.

2. 4 High temperature detection ratio during discharging (r_{THDH})

When the voltage V7 is gradually decreased and V_{CO} changes from "H" to "L" and V_{DO} changes from "H" to "L", the high temperature detection ratio during discharging (r_{THDH}) is defined by (V_{REG} − V7) / V_{REG}.

2. 5 Low temperature detection ratio during discharging (r_{THDL})

When the voltage V7 is gradually increased and V_{CO} changes from "H" to "L" and V_{DO} changes from "H" to "L", the low temperature detection ratio during discharging (r_{THDL}) is defined by (V_{REG} − V7) / V_{REG}.

2. 6 THC/DX pin voltage "H" (V_{THH})

When the voltage V6 is gradually increased after setting $(1 - r_{THDH}) \times V_{REG} < V7 < (1 - r_{THCH}) \times V_{REG}$ and V_{DO} changes from "L" to "H", V6 is defined as the THC/DX pin voltage "H" (V_{THH}).

2. 7 THC/DX pin voltage "L" (V_{THL})

When the voltage V6 is gradually decreased after setting $(1 - r_{THDH}) \times V_{REG} < V7 < (1 - r_{THCH}) \times V_{REG}$ and V_{DO} changes from "H" to "L", V6 is defined as the THC/DX pin voltage "L" (V_{THL}).

2. 8 Temperature detection delay time (t_{TH})

The temperature detection delay time (t_{TH}) is the time period from when the voltage V7 changes to 0 V until when V_{CO} changes from "H" to "L" and V_{DO} changes from "H" to "L".

■ Operation

Remark Refer to "**■ Connection Examples of Battery Protection IC**".

1. Normal status

The status when CO pin output voltage (V_{CO}) = "H", DO pin output voltage (V_{DO}) = "H" and PSO pin output voltage (V_{PSO}) = "L" is the normal status.
All the conditions mentioned below should be satisfied for returning to the normal status.

- The voltage of each of the batteries is in the range from overcharge detection voltage n (V_{CUn}) to overdischarge detection voltage n (V_{DLn}).
- CTLC pin voltage, CTLD pin voltage, and PSI pin voltage are higher than CTLC pin reverse voltage (V_{CTLC}), CTLD pin reverse voltage (V_{CTLD}), and PSI pin reverse voltage (V_{PSI}), respectively.
- Either (1) or (2) below is satisfied for TH pin voltage (V_{TH}).

(1) When $V_{THC/DX} \geq V_{THH}$: $(1 - r_{THCH}) \times V_{REG} < V_{TH} < (1 - r_{THCL}) \times V_{REG}$
(2) When $V_{THC/DX} \leq V_{THL}$: $(1 - r_{THDH}) \times V_{REG} < V_{TH} < (1 - r_{THDL}) \times V_{REG}$

Caution After the battery is connected, there may be cases when discharging cannot be performed. In this case, the S-8255B Series returns to the normal status when the following condition is satisfied.

- **Changing the PSI pin voltage to be $V_{DS} \rightarrow 0$ V $\rightarrow V_{DS}$**

Remark $V_{THC/DX}$: THC/DX pin voltage
V_{THH}: THC/DX pin voltage "H"
V_{THL}: THC/DX pin voltage "L"
r_{THCH}: High temperature detection ratio during charging
r_{THCL}: Low temperature detection ratio during charging
r_{THDH}: High temperature detection ratio during discharging
r_{THDL}: Low temperature detection ratio during discharging
V_{REG}: Output voltage for temperature detection
V_{DS}: Input voltage between VDD pin and VSS pin (V1 + V2 + V3 + V4 + V5)

2. Overcharge status

When the voltage of any of the batteries exceeds the overcharge detection voltage n (V_{CUn}) and the status continues for the overcharge detection delay time (t_{CU})*1 or longer, the CO pin changes to the V_{SS} level. This is the overcharge status.

The overcharge status is released if the following condition is satisfied.

- Voltage of battery $\leq V_{CLn}$

***1.** Refer to "**4. Delay time setting**" for details.

Remark V_{CLn}: Overcharge release voltage n (n = 1 to 5)

3. Overdischarge status

When the voltage of any of the batteries falls below the overdischarge detection voltage n (V_{DLn}) and the status continues for the overdischarge detection delay time (t_{DL})*1 or longer, the DO pin changes to the V_{SS} level. This is the overdischarge status.

The overdischarge status is released if the following condition is satisfied.

- Voltage of battery $\geq V_{DUn}$

***1.** Refer to "**4. Delay time setting**" for details.

Remark V_{DUn}: Overdischarge release voltage n (n = 1 to 5)

4. Delay time setting

Users are able to set delay time for the period from when the S-8255B Series detects change in the voltage of any of the batteries until when it outputs to the CO pin or DO pin. Each delay time is determined by a resistor in the S-8255B Series and an external capacitor.
In the overchage detection, when the voltage of any of the batteries exceeds overcharge detection voltage n (V_{CUn}), the S-8255B Series starts charging to the CCT pin's capacitor (C_{CCT}) via the CCT pin internal resistance (R_{CCT}). After a certain period, the CO pin changes to the V_{SS} level when the voltage at the CCT pin reaches the CCT pin detection voltage (V_{CCT}). This period is overcharge detection delay time (t_{CU}).

t_{CU} is calculated using the following equation.

$$t_{CU}\ [s] = -\ln(1 - V_{CCT} / V_{DS}) \times C_{CCT}\ [\mu F] \times R_{CCT}\ [M\Omega]$$
$$= -\ln(1 - 0.7\ \text{typ.}) \times C_{CCT}\ [\mu F] \times 8.31\ [M\Omega]\ \text{typ.}$$
$$= 10.0\ [M\Omega]\ \text{typ.} \times C_{CCT}\ [\mu F]$$

Overdischarge detection delay time (t_{DL}) is calculated using the following equations as well.

$$t_{DL}\ [ms] = -\ln(1 - V_{CDT} / V_{DS}) \times C_{CDT}\ [\mu F] \times R_{CDT}\ [k\Omega]$$

When $C_{CCT} = C_{CDT} = 0.1\ [\mu F]$, each delay time is calculated as follows.

$$t_{CU}\ [s] = 10.0\ [M\Omega]\ \text{typ.} \times 0.1\ [\mu F] = 1.0\ [s]\ \text{typ.}$$
$$t_{DL}\ [ms] = 1000\ [k\Omega]\ \text{typ.} \times 0.1\ [\mu F] = 100\ [ms]\ \text{typ.}$$

Remark V_{DS}: Input voltage between VDD pin and VSS pin (V1 + V2 + V3 + V4 + V5)

5. 0 V Battery detection function

For detection function of self-discharged battery (0 V battery), "available" / "unavailable" is selectable.

- 0 V battery detection function "available"
  The voltage V_{CO} changes to the V_{SS} level when the voltage of any of the batteries is V_{0INHn} or lower.

Caution When the VDD pin voltage is lower than the minimum value of operation voltage between VDD pin and VSS pin (V_{DSOP}), the S-8255B Series' operation is not assured.

Remark V_{0INHn}: 0 V battery detection voltage n (n = 1 to 5)
V_{CO}: CO pin voltage

6. SEL1 pin and SEL2 pin

Switching control for 3-serial to 5-serial cell is possible by inputting voltage to the SEL1 pin and to the SEL2 pin.
Be sure to use the SEL1 pin and the SEL2 pin at the "H" or "L" level.

Table 9 Settings of SEL1 Pin and SEL2 Pin

SEL1 Pin	SEL2 Pin	Setting
"L"	"L"	5-serial cell monitoring
"L"	"H"	4-serial cell monitoring
"H"	"L"	3-serial cell monitoring
"H"	"H"	Setting inhibited

Remark "H" is the status when $V_{SEL1} \geq V_{SEL1H}$, $V_{SEL2} \geq V_{SEL2H}$, and "L" is the status when $V_{SEL1} \leq V_{SEL1L}$, $V_{SEL2} \leq V_{SEL2L}$.

V_{SEL1H}: SEL1 pin voltage "H"
V_{SEL2H}: SEL2 pin voltage "H"
V_{SEL1L}: SEL1 pin voltage "L"
V_{SEL2L}: SEL2 pin voltage "L"

7. CTLC pin and CTLD pin

The CTLC pin controls the CO pin, and the CTLD pin controls the DO pin. Thus it is possible for users to control the CO pin and the DO pin respectively. These controls precede the battery monitoring circuit.

Table 10 Status Set by CTLC Pin

CTLC Pin	CO Pin
V_{SS} level ≤ CTLC pin voltage < V_{CTLC}	V_{SS} level
V_{CTLC} ≤ CTLC pin voltage ≤ V_{DD} level	"H"

Remark V_{CTLC}: CTLC pin reverse voltage

Table 11 Status Set by CTLD Pin

CTLD Pin	DO Pin
V_{SS} level ≤ CTLD pin voltage < V_{CTLD}	V_{SS} level
V_{CTLD} ≤ CTLD pin voltage ≤ V_{DD} level	"H"

Remark V_{CTLD}: CTLD pin reverse voltage

8. PSI pin

When the PSI pin is activated, the power-saving function starts to operate, and most operations halt. In this case, the CO pin and DO pin change to the V_{SS} level, and the PSO pin changes to the V_{DD} level.

Table 12 Status Set by PSI Pin

PSI Pin	CO Pin	DO Pin	PSO Pin
V_{PSI} < PSI pin voltage ≤ V_{DD} level	"H"	"H"	V_{SS} level
V_{SS} level ≤ PSI pin voltage ≤ V_{PSI}	V_{SS} level	V_{SS} level	V_{DD} level

Remark V_{PSI}: PSI pin reverse voltage

The S-8255B Series is initialized and the power-saving function is released by deactivating the PSI pin. As a result, each detection operation is carried out after returning to the normal status.

9. Temperature detection

Serially connect an NTC and a low temperature-dependent resistor (R_{TH}) between the VDD pin and the VREG pin, and then connect their middle point to the TH pin. It allows for temperature detection at four different points: high temperature detection during charging, low temperature detection during charging, high temperature detection during discharging, low temperature detection during discharging.

When the temperature rises, according to the NTC temperature characteristics, the resistance (R_{NTC}) decreases, and the ratio between R_{NTC} and R_{TH} changes, and then the TH pin voltage (V_{TH}) increases.
When the temperature falls, according to the NTC temperature characteristics, the resistance (R_{NTC}) increases, and the ratio between R_{NTC} and R_{TH} changes, and then the TH pin voltage (V_{TH}) decreases.
The temperature detection during charging and temperature detection during discharging switch by comparing THC/DX pin voltage ($V_{THC/DX}$) and either of THC/DX pin voltage "H" or "L" (V_{THH}, V_{THL}).
If the relation between R_{NTC}, R_{TH}, and $V_{THC/DX}$ satisfies the itemized condition in **Table 13** in each temperature detection, and each status continues for the temperature detection delay time (t_{TH}) or longer, the CO pin changes to the V_{SS} level and the DO pin changes to the "H" or V_{SS} level. This is the temperature protection status.
If the itemized condition in **Table 13** is not satisfied in each temperature detection, and each status continues for t_{TH} or longer, the temperature protection status is released.

Table 13 Conditions for Each Temperature Detection

<table>
<tr><th>Item</th><th>TH Pin</th><th>THC/DX Pin</th><th>CO Pin</th><th>DO Pin</th></tr>
<tr><td>High temperature detection during charging</td><td>$r_{THCH} \leq R_{TH} / (R_{NTC} + R_{TH})$</td><td>$V_{THC/DX} \geq V_{THH}$</td><td rowspan="4">$V_{SS}$ level</td><td rowspan="2">"H"</td></tr>
<tr><td>Low temperature detection during charging</td><td>$r_{THCL} \geq R_{TH} / (R_{NTC} + R_{TH})$</td><td>$V_{THC/DX} \geq V_{THH}$</td></tr>
<tr><td>High temperature detection during discharging</td><td>$r_{THDH} \leq R_{TH} / (R_{NTC} + R_{TH})$</td><td>$V_{THC/DX} \leq V_{THL}$</td><td rowspan="2">$V_{SS}$ level</td></tr>
<tr><td>Low temperature detection during discharging</td><td>$r_{THDL} \geq R_{TH} / (R_{NTC} + R_{TH})$</td><td>$V_{THC/DX} \leq V_{THL}$</td></tr>
</table>

Remark r_{THCH}: High temperature detection ratio during charging
r_{THCL}: Low temperature detection ratio during charging
r_{THDH}: High temperature detection ratio during discharging
r_{THDL}: Low temperature detection ratio during discharging

The detection temperature can be set according to the NTC and R_{TH} characteristics.
For example, if R_{NTC}*1 and R_{TH} (10 kΩ) are connected to S-8255BAA, each detection temperature is as follows.

Table 14

Item	Temperature Detection Ratio	R_{NTC}	Detection Temperature
Temperature for high temperature detection during charging	r_{THCH} = 0.670	4.9 kΩ	45°C
Temperature for low temperature detection during charging	r_{THCL} = 0.270	27.0 kΩ	0°C
Temperature for high temperature detection during discharging	r_{THDH} = 0.795	2.6 kΩ	65°C
Temperature for low temperature detection during discharging	r_{THDL} = 0.190	42.6 kΩ	−10°C

***1.** The calculation method for R_{NTC} is as follows.

$$r_{THCL} = R_{TH} / (R_{NTC} + R_{TH})$$
$$R_{NTC} = R_{TH} / r_{THCL} - R_{TH} = 10\ \text{k}\Omega / 0.270 - 10\ \text{k}\Omega = 27.0\ \text{k}\Omega$$

When low temperature during charging is detected, R_{NTC} = 27.0 kΩ, so detection temperature = 0°C according to the R_{NTC} characteristics shown in **Figure 5**.

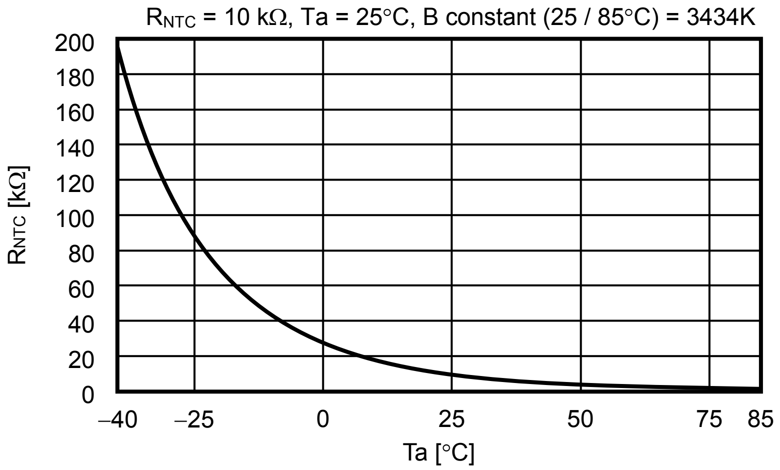
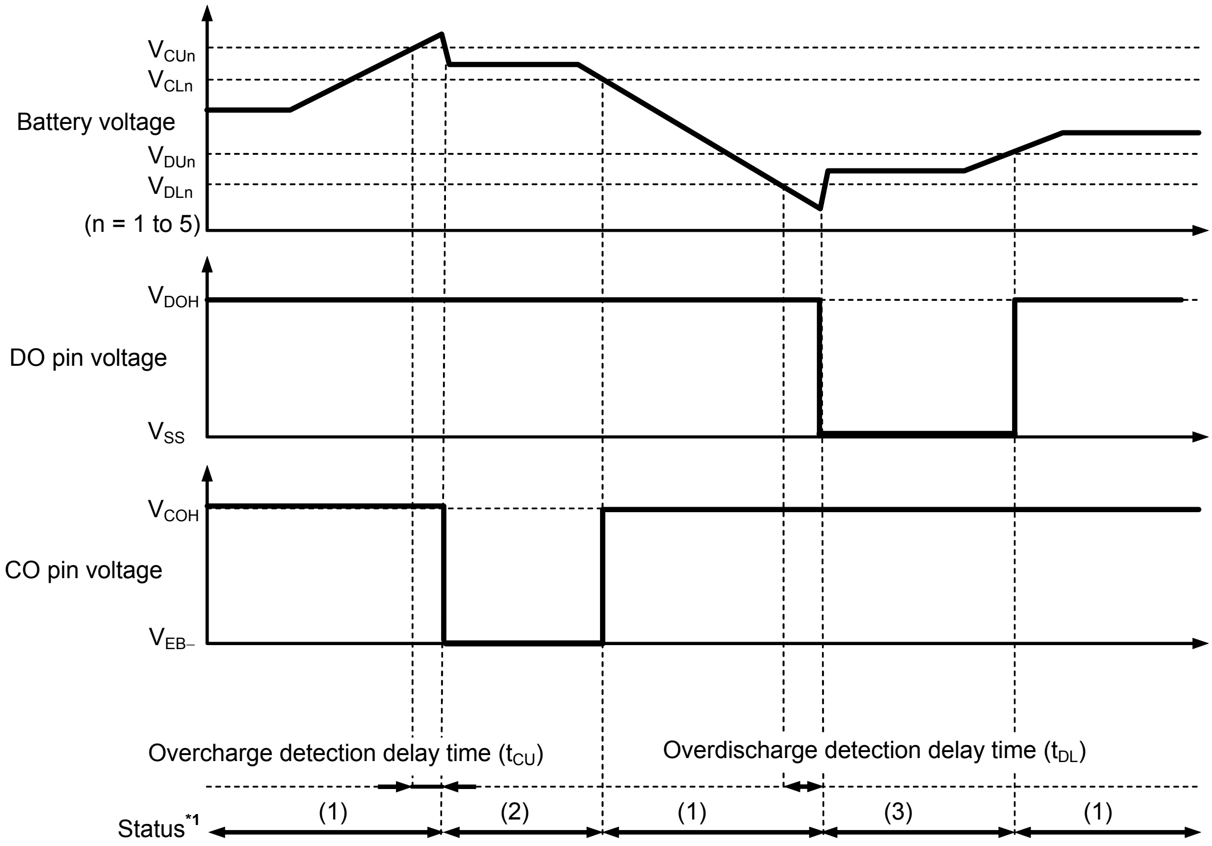


Figure 5 Example of R_{NTC} Characteristics

Remark Temperature detection is carried out intermittently for 512 ms typ. per cycle, of which 1 ms typ. is the detection operation period.
The VREG pin voltage is output only during detection operation. During other periods, the VREG pin is at the V_{DD} level.
Regarding details of intermittent operation, refer to "**2. Temperature detection (High temperature detection during charging)**" in "**■ Timing Charts**".

■ Timing Charts

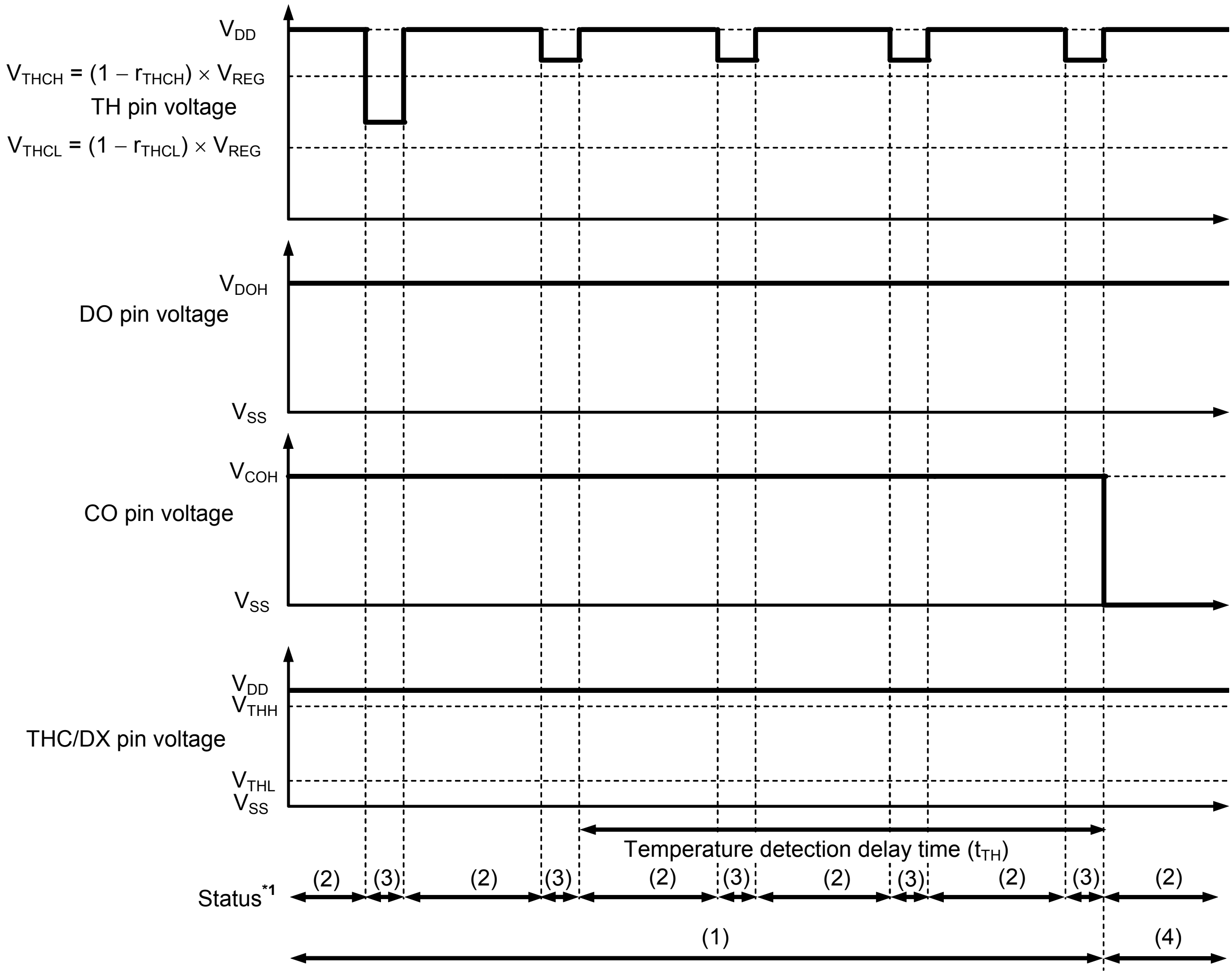
1. Overcharge detection, overdischarge detection



***1.** (1) : Normal status
(2) : Overcharge status
(3) : Overdischarge status

Figure 6

2. Temperature detection (High temperature detection during charging)

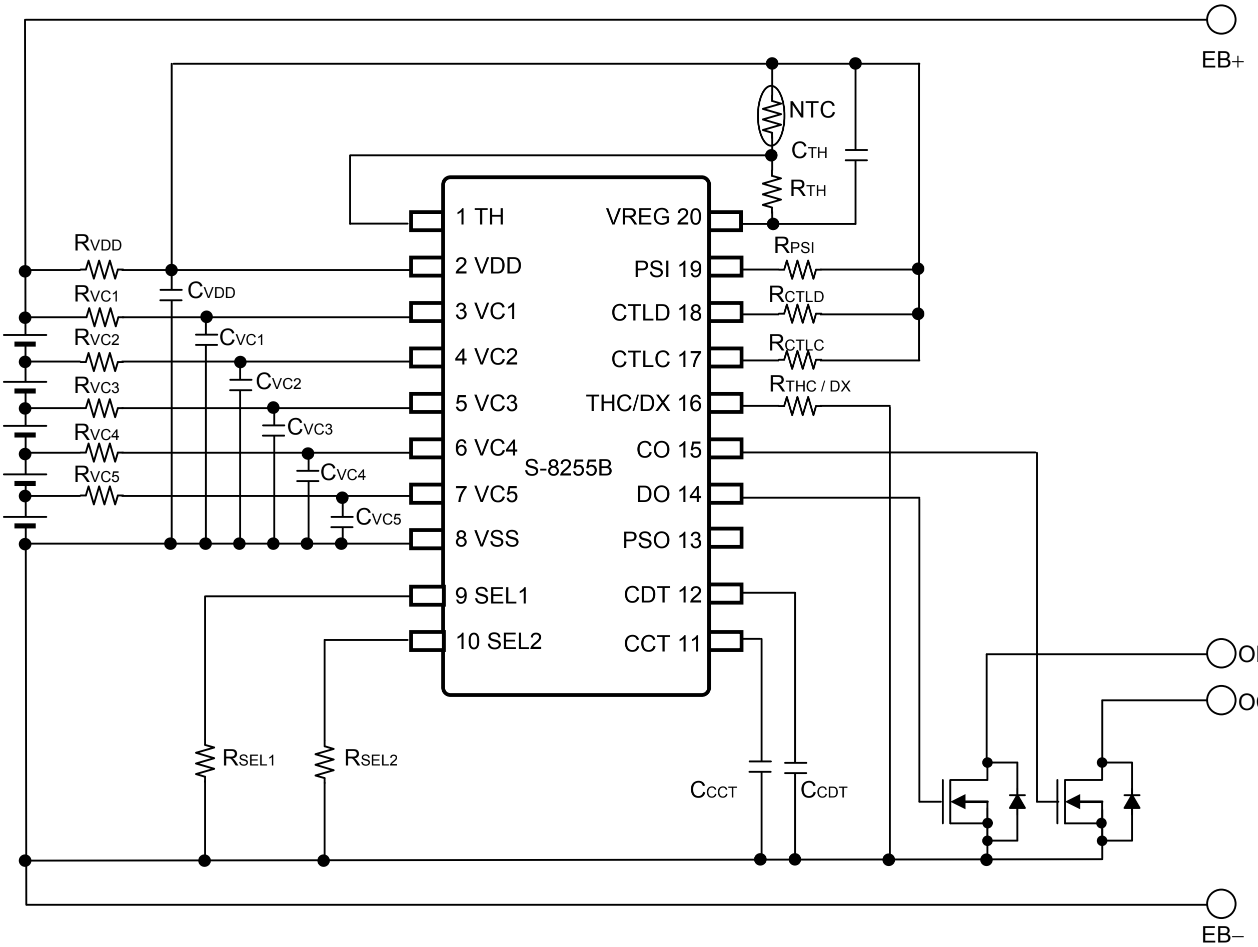


***1.** (1) : Normal status
(2) : Temperature detection sleep time
(3) : Temperature detection awake time
(4) : Temperature protection status

Figure 7

■ Connection Examples of Battery Monitoring IC

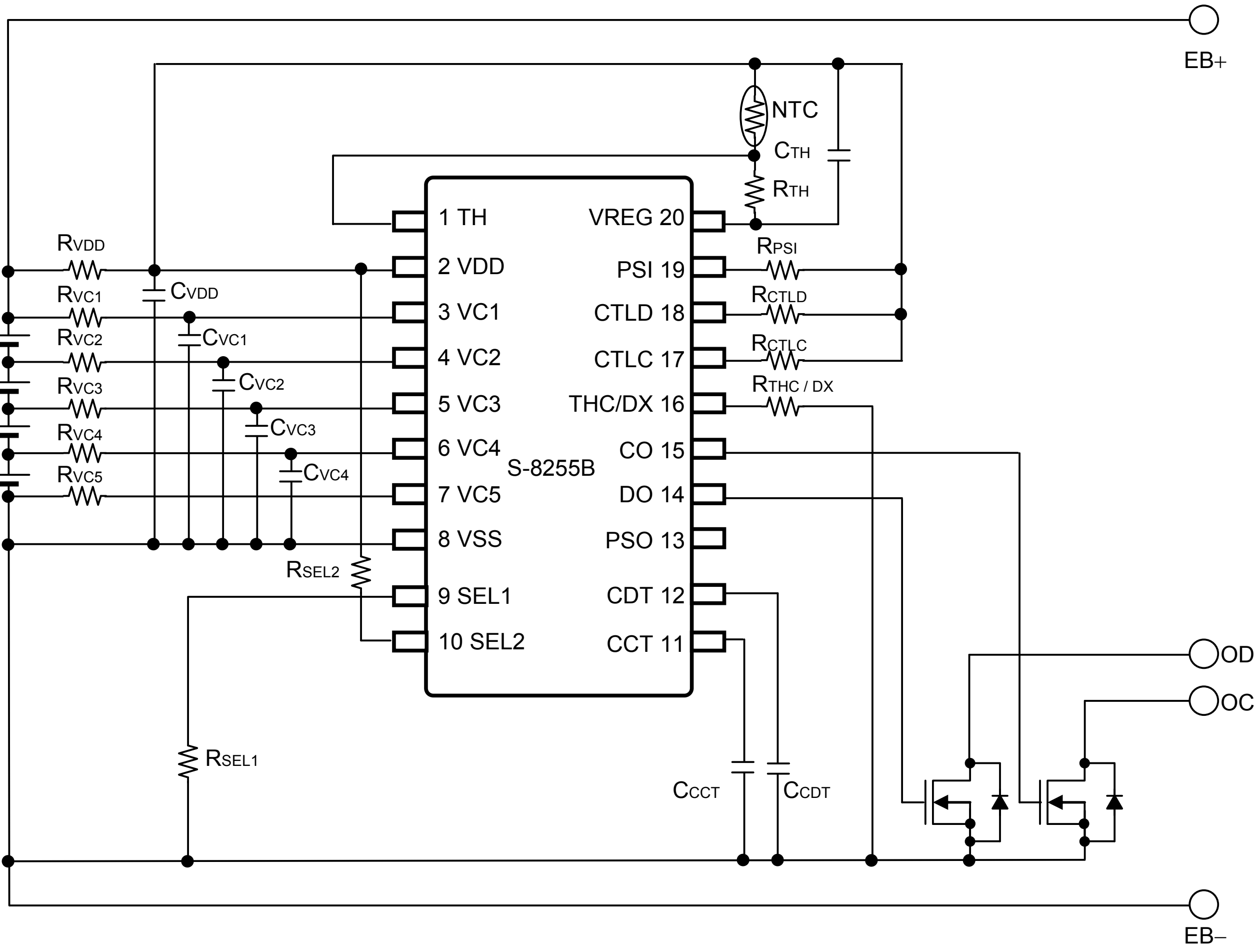
1. S-8255B Series (5-serial cell)



Remark Regarding the recommended values for external components, refer to "**Table 15 Constants for External Components**".

Figure 8

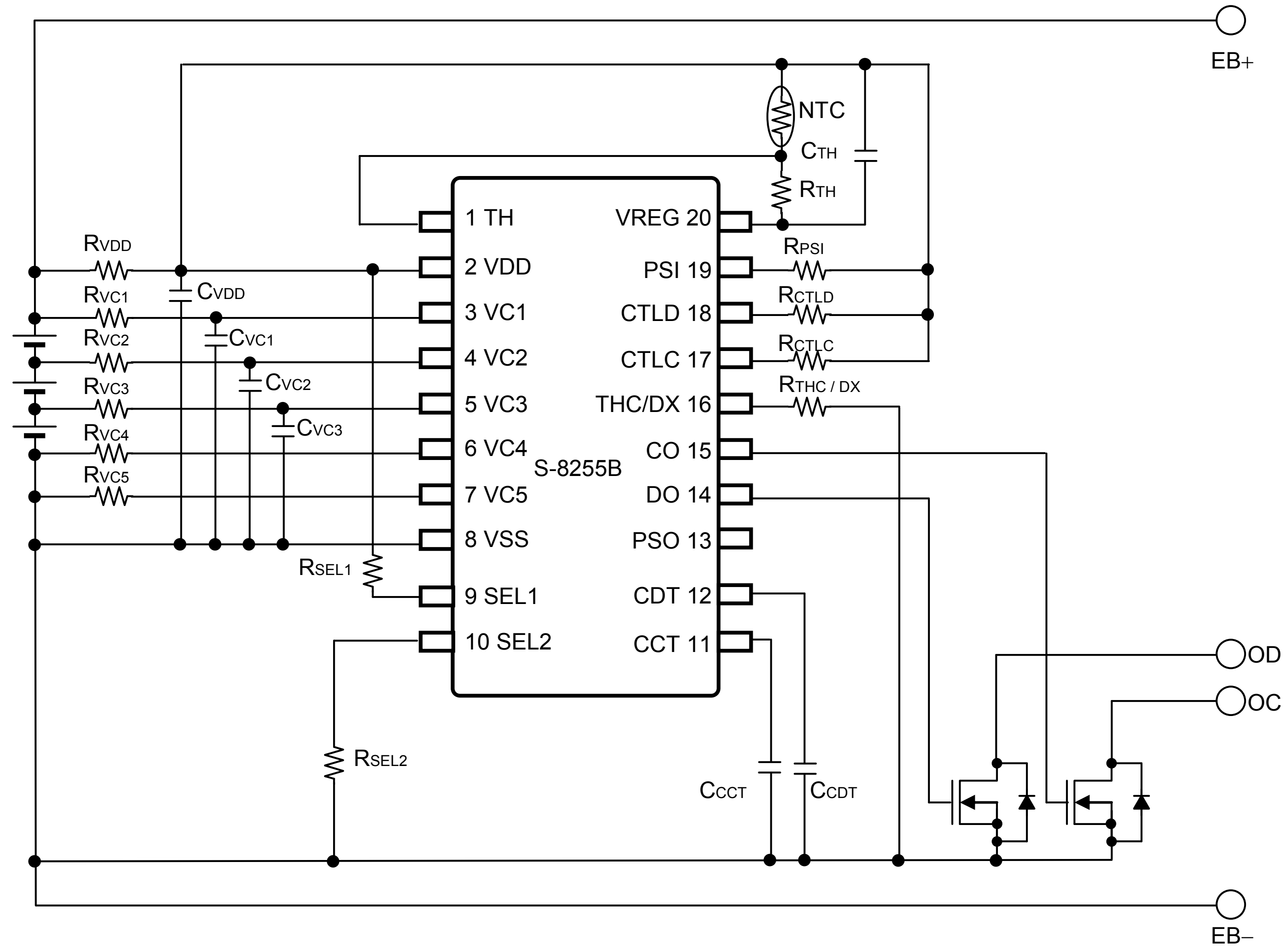
2. S-8255B Series (4-serial cell)



Remark Regarding the recommended values for external components, refer to "**Table 15 Constants for External Components**".

Figure 9

3. S-8255B Series (3-serial cell)



Remark Regarding the recommended values for external components, refer to "**Table 15 Constants for External Components**".

Figure 10

Table 15 Constants for External Components

Symbol	Min.	Typ.	Max.	Unit
R_{VDD} *1	68	100	100	Ω
R_{VCn} (n = 1 to 5) *1	0.68	1.00	1.00	kΩ
R_{SEL1}, R_{SEL2}	1	1	–	kΩ
$R_{THC/DX}$	1.0	1.0	–	kΩ
NTC	–	10	–	kΩ
R_{TH}	–	10	–	kΩ
C_{VDD} *1	0.68	1.00	10.00	μF
C_{VCn} (n = 1 to 5) *1	0.068	0.100	1.000	μF
C_{CCT}	0.01	0.10	–	μF
C_{CDT}	0.01	0.10	–	μF
C_{TH}	0.1	0.1	0.1	μF

***1.** $R_{VDD} \times C_{VDD}$ = 100 μF • Ω is recommended.
Set filter constants to satisfy $R_{VC1} \times C_{VC1} = R_{VC2} \times C_{VC2} = R_{VC3} \times C_{VC3} = R_{VC4} \times C_{VC4} = R_{VC5} \times C_{VC5} = R_{VDD} \times C_{VDD}$.

Caution 1. The above constants may be changed without notice.

2. Sufficient evaluation of transient power supply fluctuation and overcurrent protection function with the actual application is needed to determine the proper constants when setting the filter constants between the VDD pin and VSS pin. Contact our sales office if setting the constants between the VDD pin and VSS pin to anything other than the recommended values.

3. It has not been confirmed whether the operation is normal or not in circuits other than the connection examples. In addition, the connection examples and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constants.

■ Precautions

- The application conditions for the input voltage, output voltage, and load current should not exceed the power dissipation.

- Batteries can be connected in any order; however, there may be cases when discharging cannot be performed after a battery is connected. In this case, the S-8255B Series returns to the normal status when the following condition is satisfied.

  - Changing the PSI pin voltage to be $V_{DS} \rightarrow 0$ V $\rightarrow V_{DS}$

  Remark V_{DS}: Input voltage between VDD pin and VSS pin (V1 + V2 + V3 + V4 + V5)

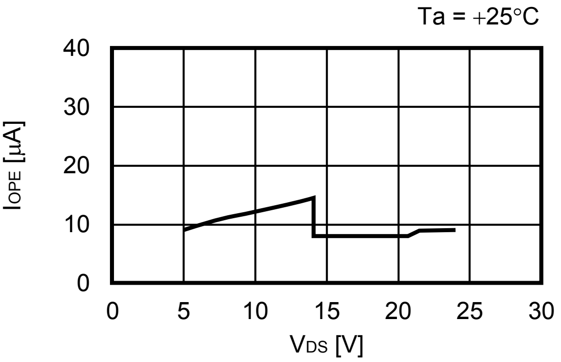
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.

- ABLIC Inc. claims no responsibility for any disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

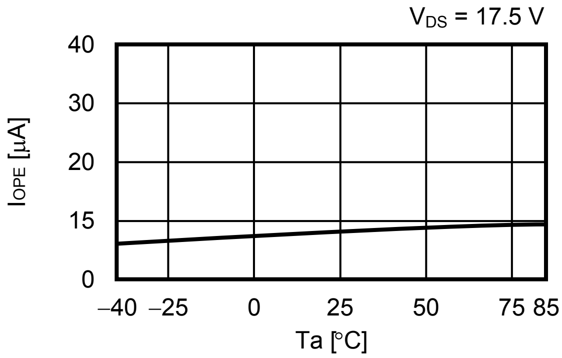
■ Characteristics (Typical Data)

1. Current consumption

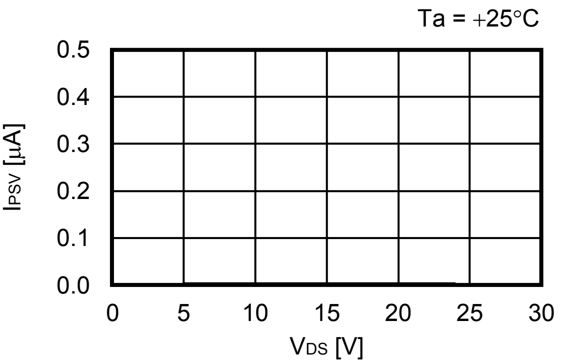
1. 1 I_{OPE} vs. V_{DS}



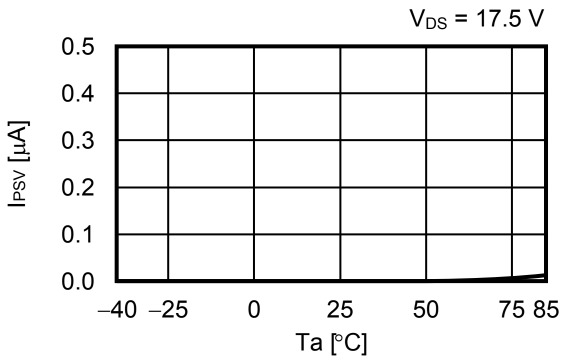
1. 2 I_{OPE} vs. Ta



1. 3 I_{PSV} vs. V_{DS}

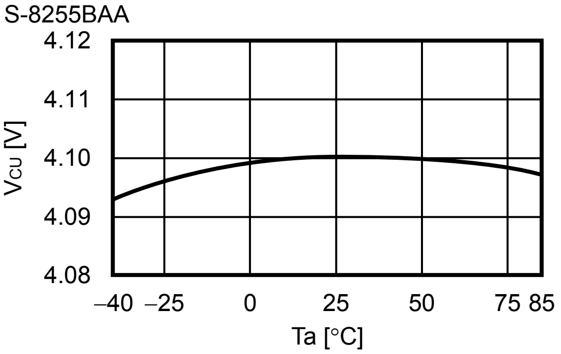


1. 4 I_{PSV} vs. Ta

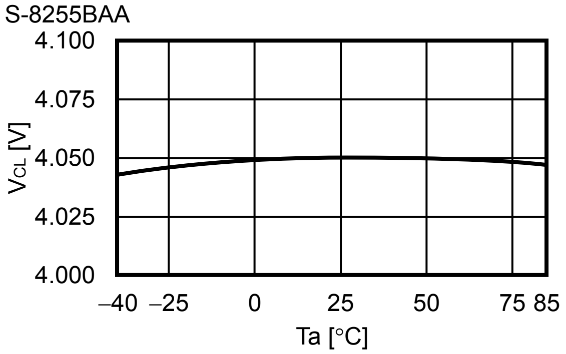


2. Detection voltage, release voltage

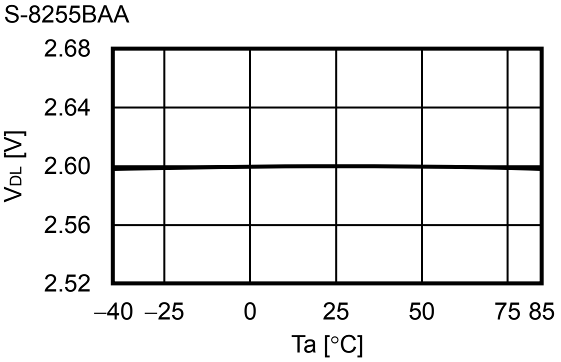
2. 1 V_{CU} vs. Ta



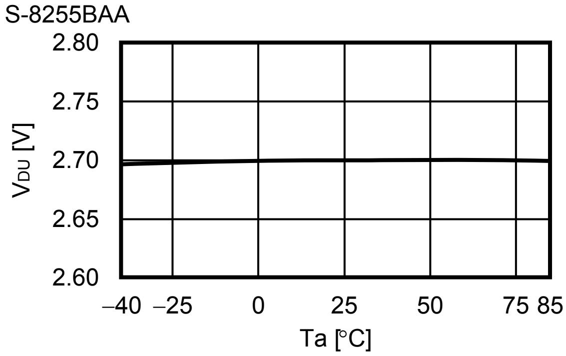
2. 2 V_{CL} vs. Ta



2. 3 V_{DL} vs. Ta

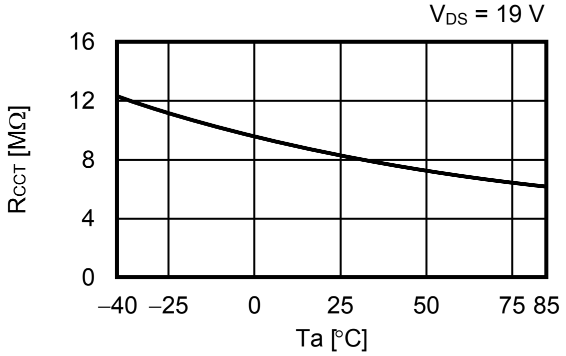


2. 4 V_{DU} vs. Ta

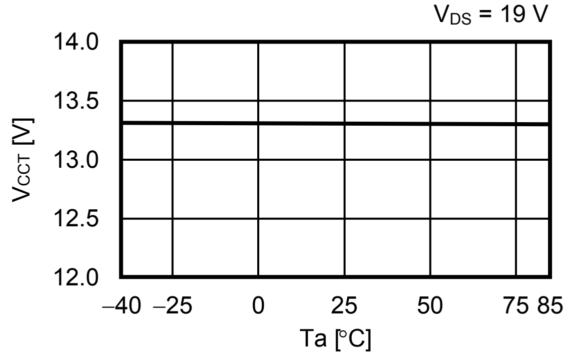


3. Delay time function

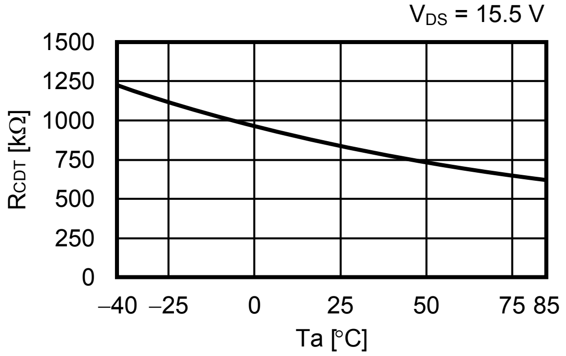
3. 1 R_{CCT} vs. Ta



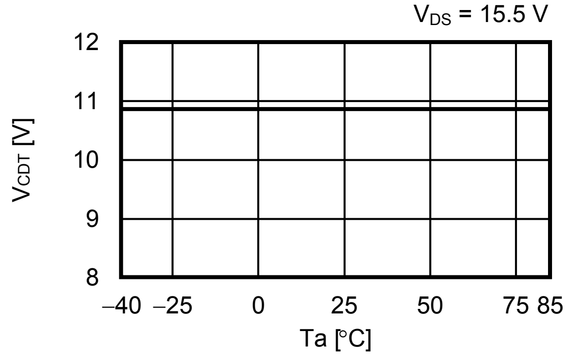
3. 2 V_{CCT} vs. Ta



3. 3 R_{CDT} vs. Ta

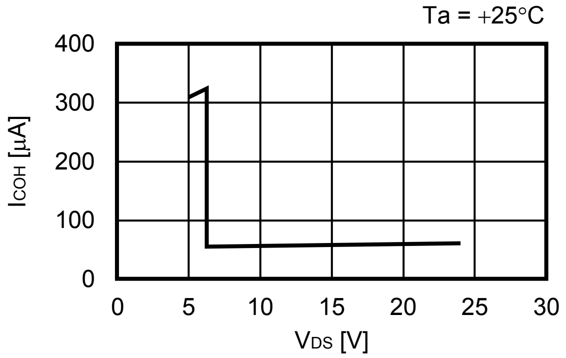


3. 4 V_{CDT} vs. Ta

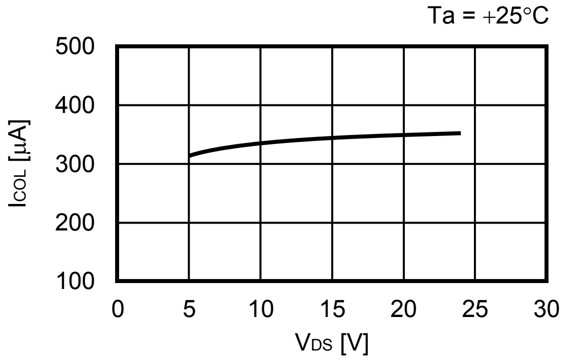


4. Output pin

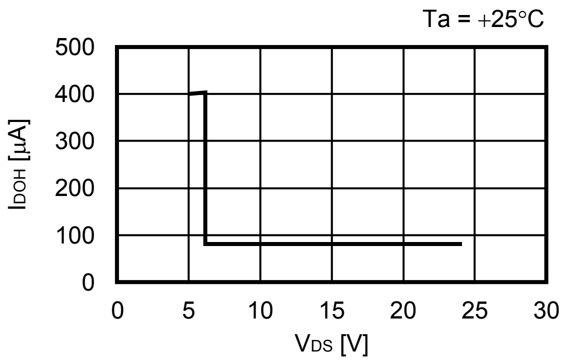
4. 1 I_{COH} vs. V_{DS}



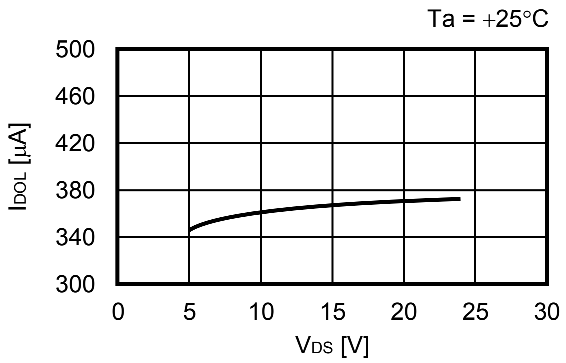
4. 2 I_{COL} vs. V_{DS}



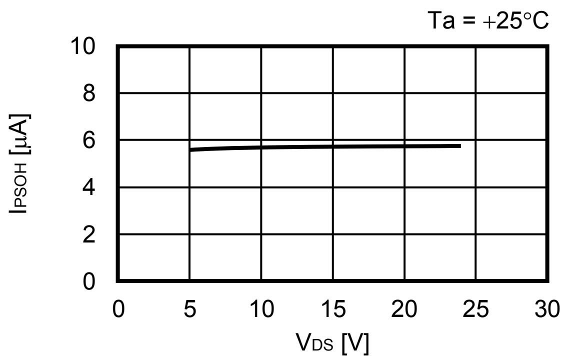
4. 3 I_{DOH} vs. V_{DS}



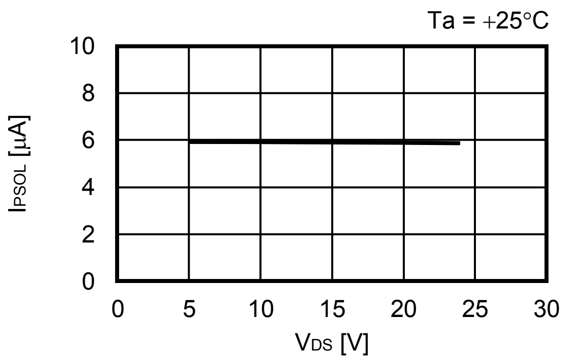
4. 4 I_{DOL} vs. V_{DS}



4. 5 I_{PSOH} vs. V_{DS}

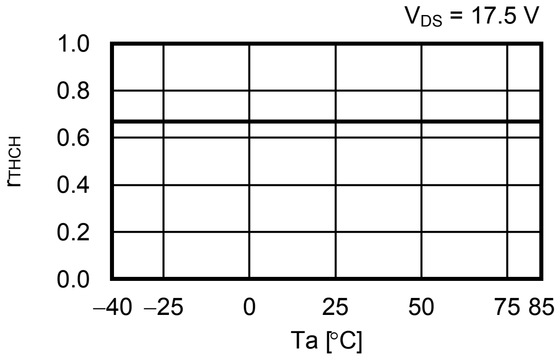


4. 6 I_{PSOL} vs. V_{DS}

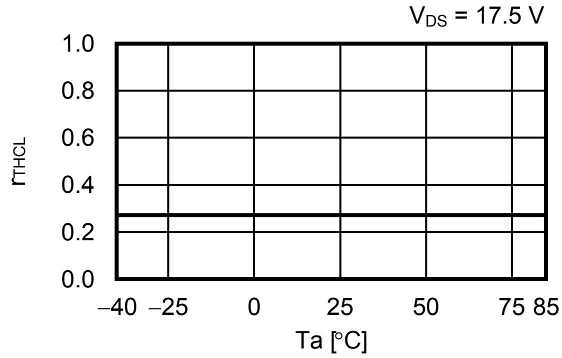


5. Temperature detection function

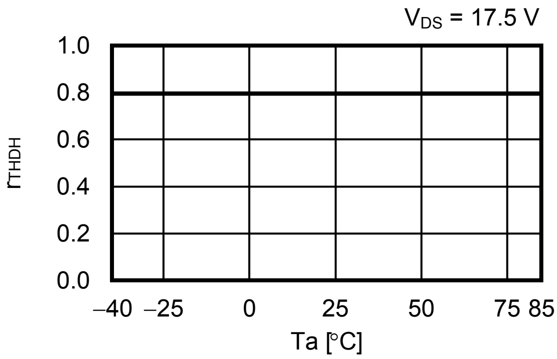
5. 1 r_{THCH} vs. Ta



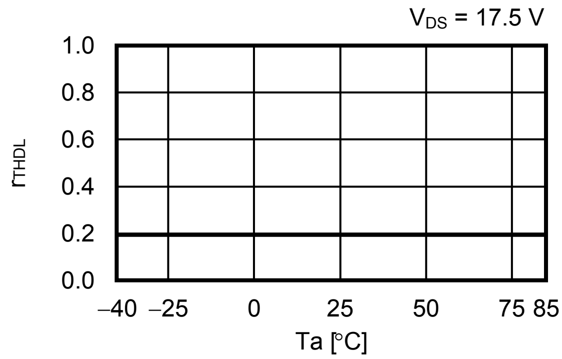
5. 2 r_{THCL} vs. Ta



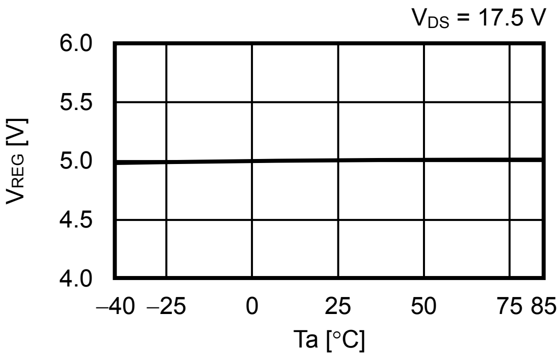
5. 3 r_{THDH} vs. Ta



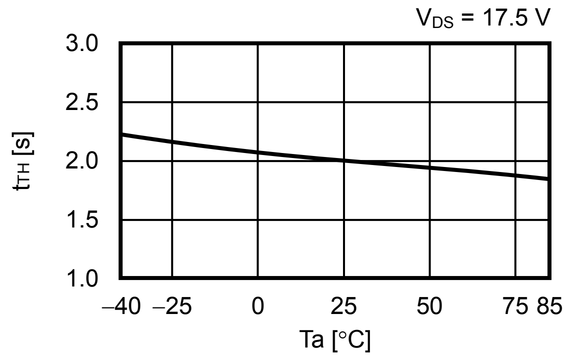
5. 4 r_{THDL} vs. Ta



5. 5 V_{REG} vs. Ta

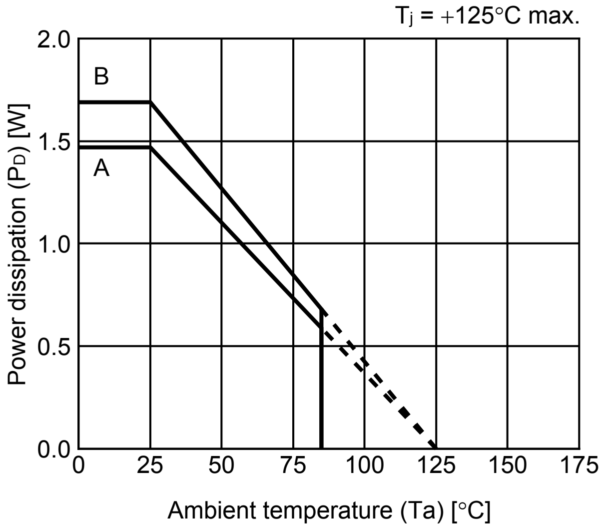


5. 6 t_{TH} vs. Ta



■ Power Dissipation

20-Pin TSSOP

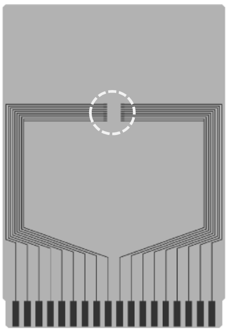


Board	Power Dissipation (P_D)
A	1.47 W
B	1.69 W
C	–
D	–
E	–

20-Pin TSSOP Test Board

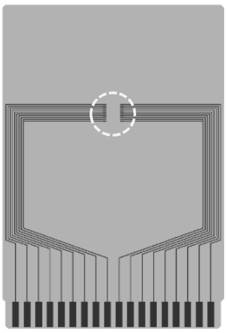
IC Mount Area

(1) Board A



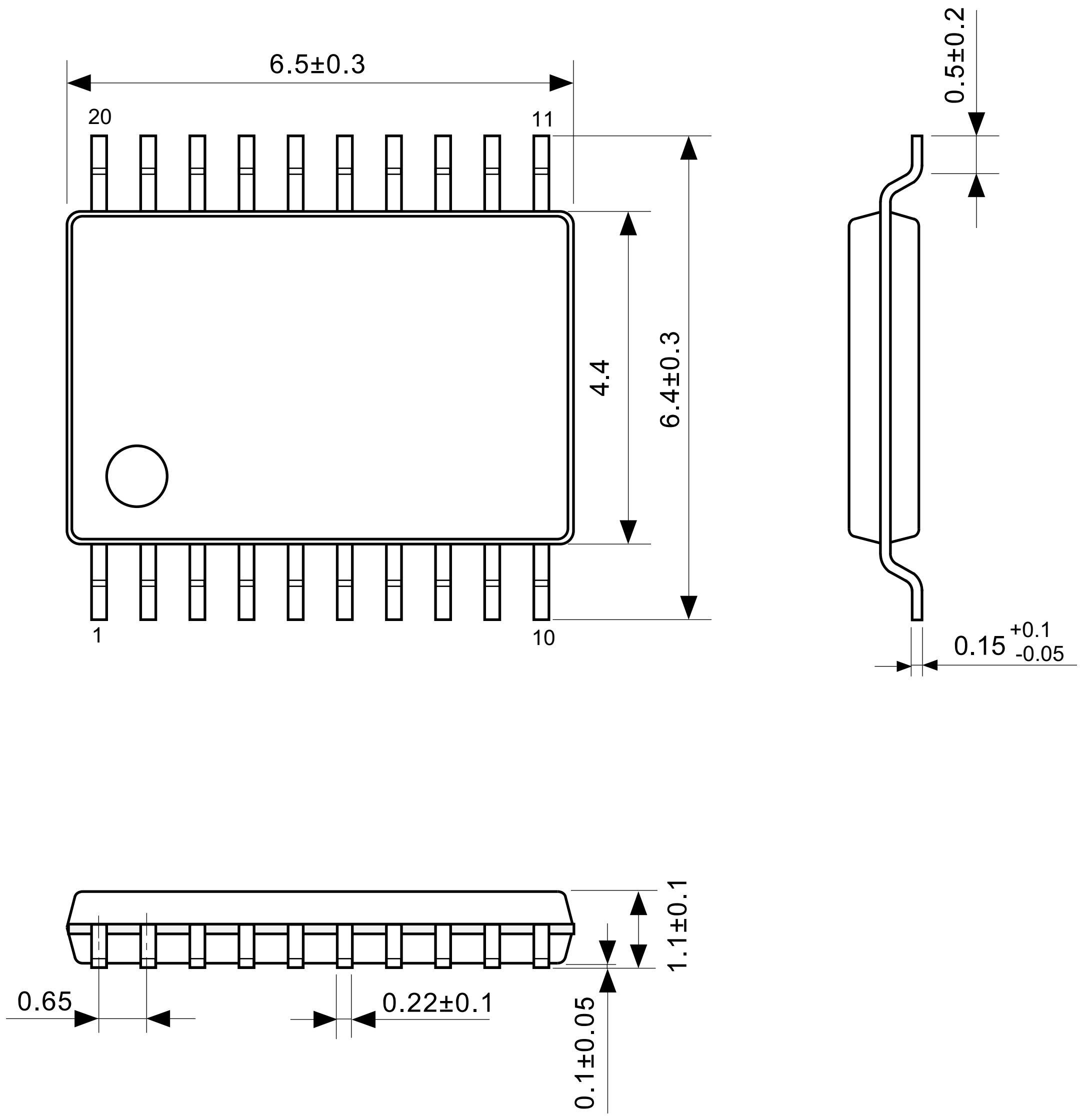
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		2
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	-
	3	-
	4	74.2 x 74.2 x t0.070
Thermal via		-

(2) Board B



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-

No. TSSOP20-A-Board-SD-1.0



No. FT020-B-P-SD-1.0

TITLE	TSSOP20-B-PKG Dimensions
No.	FT020-B-P-SD-1.0
ANGLE	
UNIT	mm

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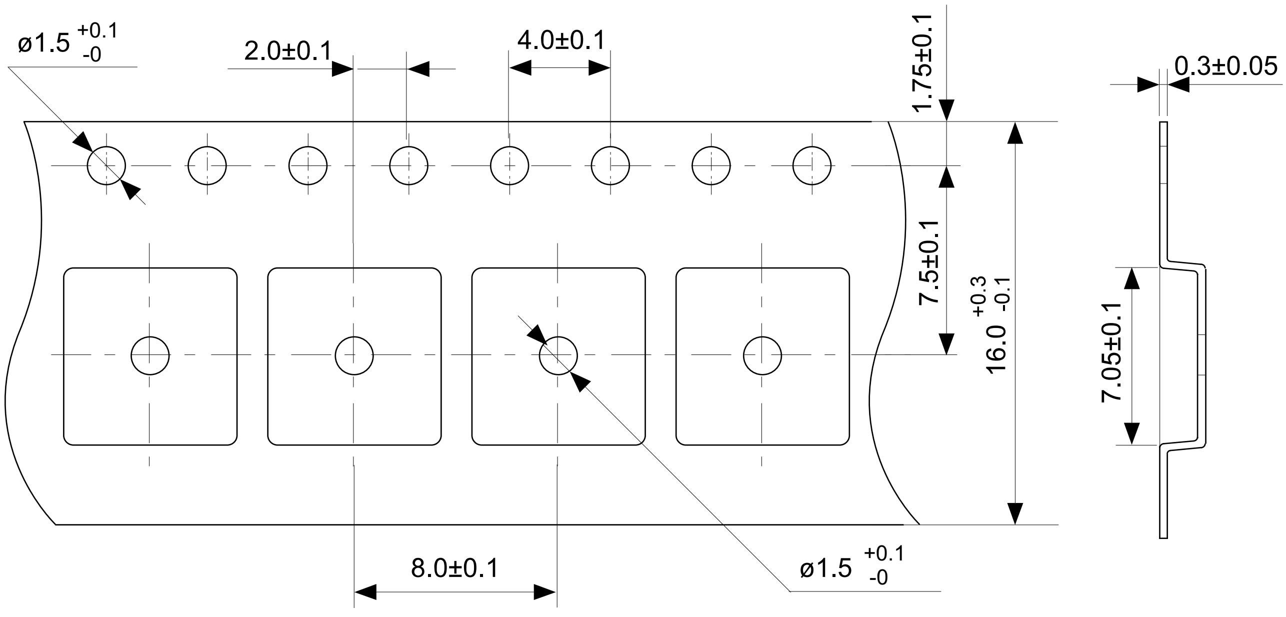

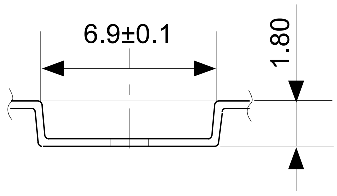

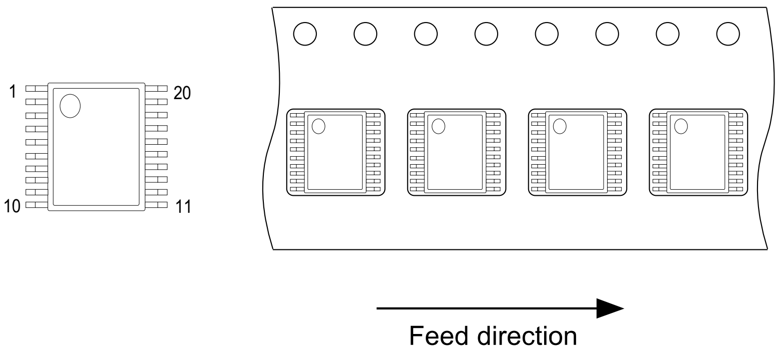

No. FT020-B-C-SD-1.0

TITLE	TSSOP20-B-Carrier Tape
No.	FT020-B-C-SD-1.0
ANGLE	
UNIT	mm

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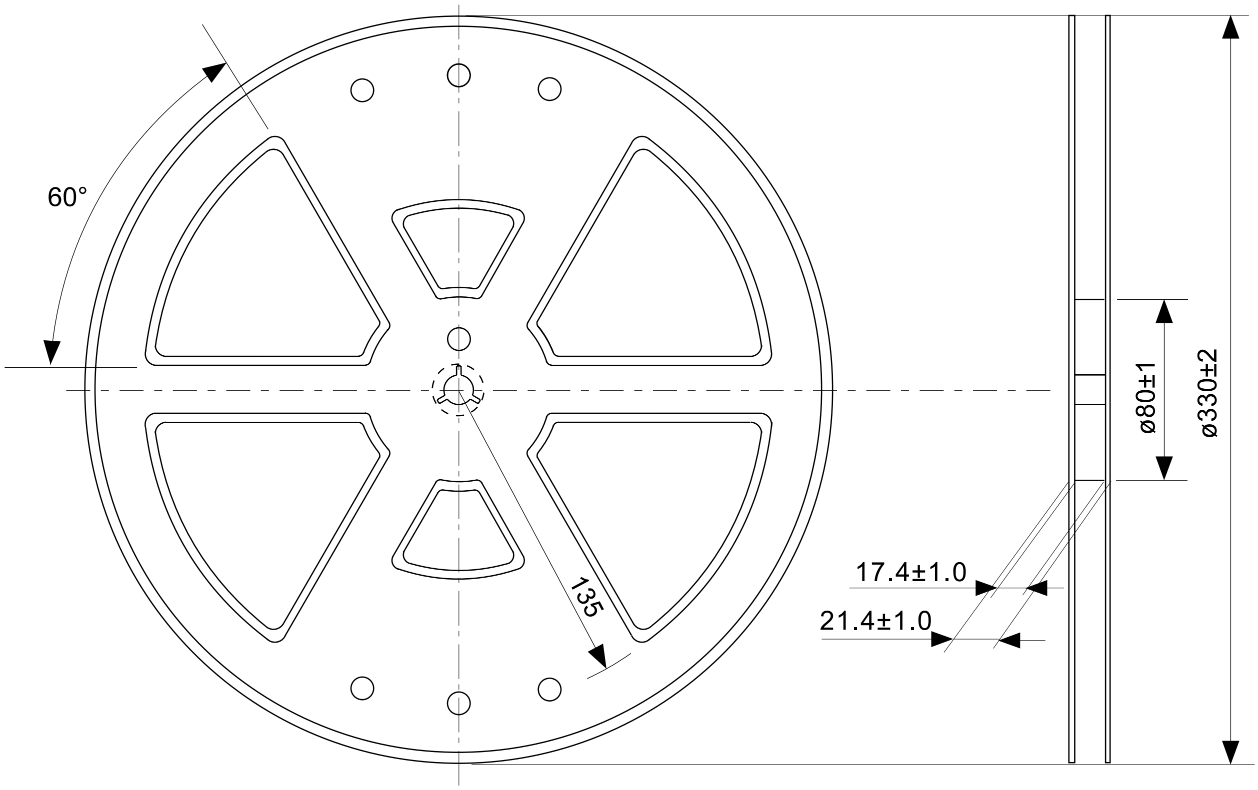
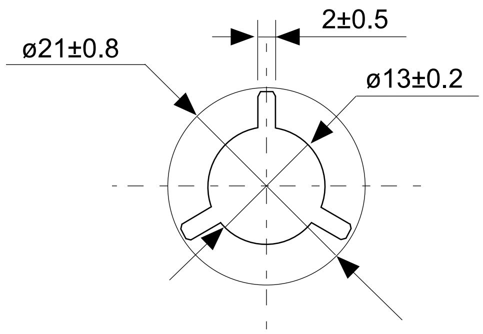


Enlarged drawing in the central part



No. FT020-B-R-SD-1.0

TITLE	TSSOP20-B-Reel		
No.	FT020-B-R-SD-1.0		
ANGLE		QTY.	4.000
UNIT	mm		

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2.4-2019.07